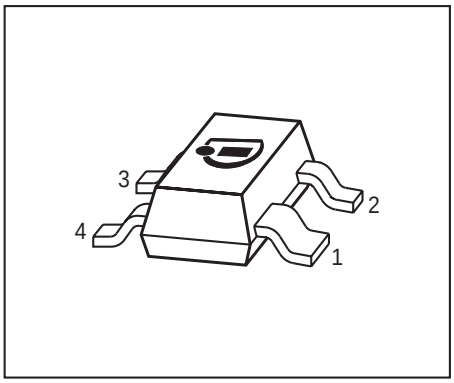
NPN Silicon RF Transistor*



- For low noise, low distortion broadband amplifiers in antenna and telecommunications systems up to 1.5 GHz at collector currents from 20 mA to 80 mA
- Power amplifier for DECT and PCN systems
- f_T = 7.5 GHz, F = 1.3 dB at 900 MHz
- Pb-free (RoHS compliant) package[1)]
- Qualified according AEC Q101

* Short term description

ESD (**E**lectro**s**tatic **d**ischarge) sensitive device, observe handling precaution!

Type	Marking	Pin Configuration						Package
BFP196	RIs	1 = C	2 = E	3 = B	4 = E	-	-	SOT143

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	12	V
Collector-emitter voltage	V_{CES}	20	
Collector-base voltage	V_{CBO}	20	
Emitter-base voltage	V_{EBO}	2	
Collector current	I_C	150	mA
Base current	I_B	15	
Total power dissipation[2)] $T_S \leq 77$ °C	P_{tot}	700	mW
Junction temperature	T_j	150	°C
Ambient temperature	T_A	-65 ... 150	
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point[3)]	R_{thJS}	≤ 105	K/W

[1] Pb-containing package may be available upon special request

[2] T_S is measured on the collector lead at the soldering point to the pcb

[3] For calculation of R_{thJA} please refer to Application Note Thermal Resistance

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Electrical Characteristics at T_A = 25°C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage I_C = 1 mA, I_B = 0	$V_{(BR)CEO}$	12	-	-	V
Collector-emitter cutoff current V_{CE} = 20 V, V_{BE} = 0	I_{CES}	-	-	100	µA
Collector-base cutoff current V_{CB} = 10 V, I_E = 0	I_{CBO}	-	-	100	nA
Emitter-base cutoff current V_{EB} = 1 V, I_C = 0	I_{EBO}	-	-	1	µA
DC current gain- I_C = 50 mA, V_{CE} = 8 V, pulse measured	h_{FE}	70	100	140	-

Electrical Characteristics at T_A = 25°C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics (verified by random sampling)					
Transition frequency I_C = 70 mA, V_{CE} = 8 V, f = 500 MHz	f_T	5	7.5	-	GHz
Collector-base capacitance V_{CB} = 10 V, f = 1 MHz, V_{BE} = 0 , emitter grounded	C_{cb}	-	0.83	1.3	pF
Collector emitter capacitance V_{CE} = 10 V, f = 1 MHz, V_{BE} = 0 , base grounded	C_{ce}	-	0.35	-	
Emitter-base capacitance V_{EB} = 0.5 V, f = 1 MHz, V_{CB} = 0 , collector grounded	C_{eb}	-	3.9	-	
Noise figure I_C = 20 mA, V_{CE} = 8 V, Z_S = Z_{Sopt} , f = 900 MHz I_C = 20 mA, V_{CE} = 8 V, Z_S = Z_{Sopt} , f = 1.8 GHz	F	 - -	 1.3 2.3	 - -	dB
Power gain, maximum available[1)] I_C = 50 mA, V_{CE} = 8 V, Z_S = Z_{Sopt} , Z_L = Z_{Lopt} , f = 900 MHz I_C = 50 mA, V_{CE} = 8 V, Z_S = Z_{Sopt} , Z_L = Z_{Lopt} , f = 1.8 GHz	G_{ma}	 - -	 16.5 10.5	 - -	
Transducer gain I_C = 50 mA, V_{CE} = 8 V, Z_S = Z_L = 50Ω , f = 900 MHz I_C = 50 mA, V_{CE} = 8 V, Z_S = Z_L = 50Ω , f = 1.8 GHz	$\lvert S_{21e}\rvert^2$	 - -	 13 7	 - -	dB

[1] $G_{ma} = |S_{21} / S_{12}| (k-(k^2-1)^{1/2})$

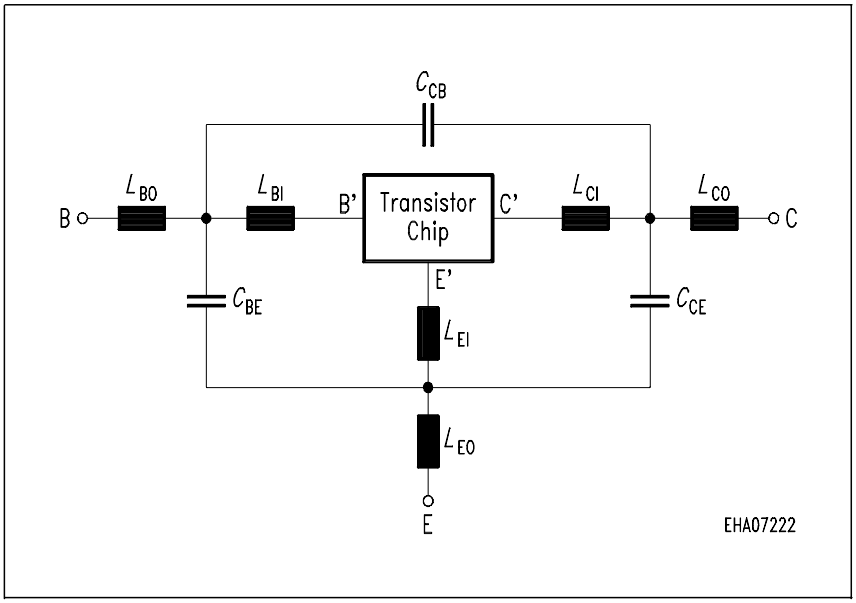
SPICE Parameter (Gummel-Poon Model, Berkley-SPICE 2G.6 Syntax):

Transistor Chip Data:

IS =	1.7264	fA	BF =	125	-	NF =	0.80012	-
VAF =	20	V	IKF =	0.4294	A	ISE =	119.22	fA
NE =	1.1766	-	BR =	10.584	-	NR =	0.94288	-
VAR =	3.8128	V	IKR =	0.019551	A	ISC =	4.8666	fA
NC =	0.88299	-	RB =	1.2907	Ω	IRB =	0.084011	mA
RBM =	1	Ω	RE =	0.75103	-	RC =	0.27137	Ω
CJE =	13.325	fF	VJE =	0.7308	V	MJE =	0.33018	-
TF =	23.994	ps	XTF =	0.44322	-	VTF =	0.1	V
ITF =	1.9775	mA	PTF =	0	deg	CJC =	1667	fF
VJC =	0.73057	V	MJC =	0.3289	-	XCJC =	0.29998	-
TR =	2.2413	ns	CJS =	0	fF	VJS =	0.75	V
MJS =	0	-	NK =	0	-	EG =	1.11	eV
XTI =	3	-	FC =	0.50922		TNOM	300	K

All parameters are ready to use, no scalling is necessary. Extracted on behalf of Infineon Technologies AG by: Institut für Mobil- und Satellitentechnik (IMST)

Package Equivalent Circuit:

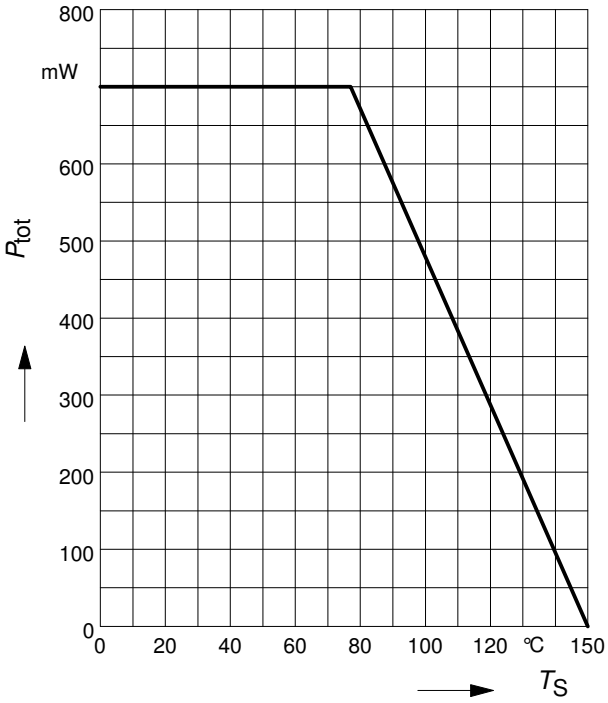


L_{BI} =	0.84	nH
L_{BO} =	0.65	nH
L_{EI} =	0.31	nH
L_{EO} =	0.14	nH
L_{CI} =	0.07	nH
L_{CO} =	0.42	nH
C_{BE} =	145	fF
C_{CB} =	19	fF
C_{CE} =	281	fF

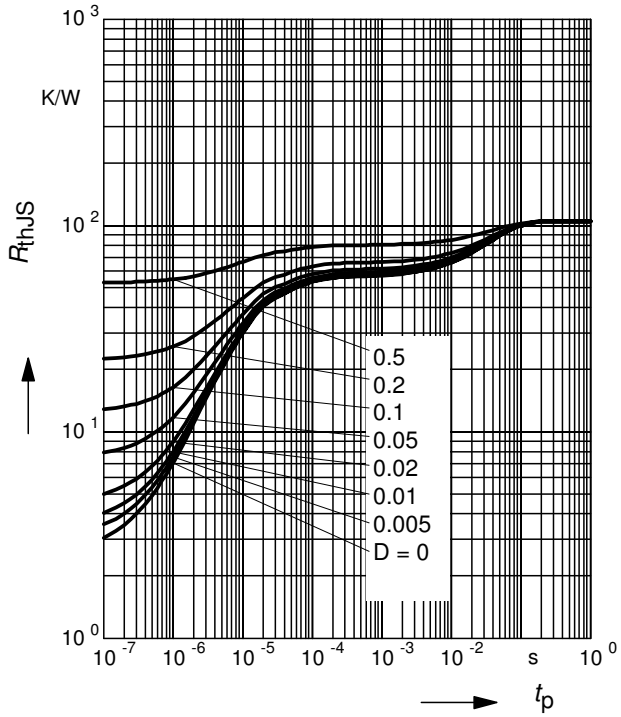
Valid up to 6GHz

For examples and ready to use parameters please contact your local Infineon Technologies distributor or sales office to obtain a Infineon Technologies CD-ROM or see Internet: http://www.infineon.com

Total power dissipation $P_{tot} = f(T_S)$

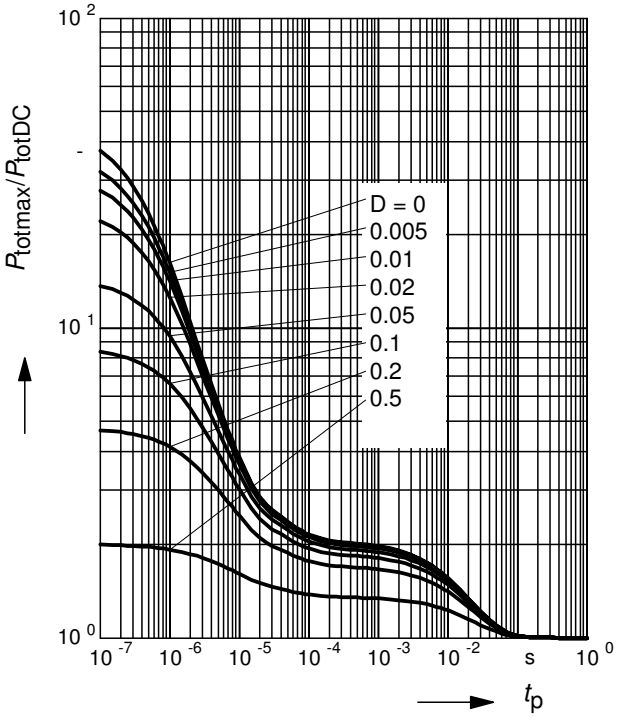


Permissible Pulse Load $R_{thJS} = f(t_p)$

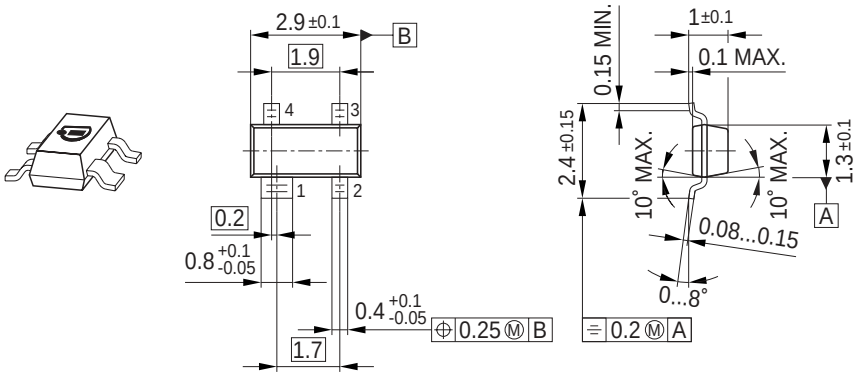


Permissible Pulse Load

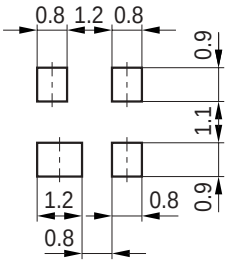
$P_{totmax}/P_{totDC} = f(t_p)$



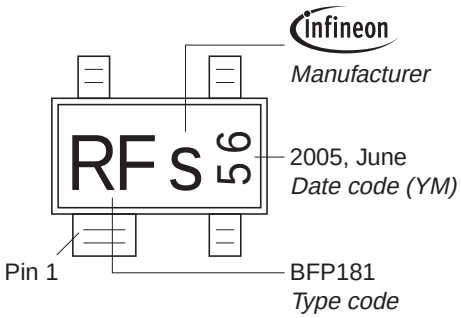
Package Outline



Foot Print

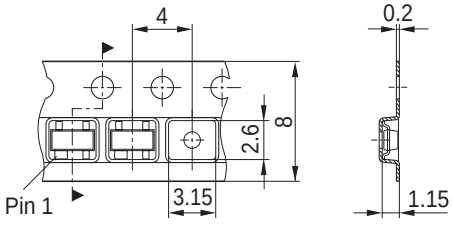


Marking Layout (Example)



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel
Reel ø330 mm = 10.000 Pieces/Reel



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